



DESCRIPTION

The AM2301A is available in SOT-23S package.

FEATURES

- $V_{DS} = -20V$
- $R_{DS(ON)}, V_{GS}@-4.5V, I_{DS}@-4.7A=70m\Omega$
- $R_{DS(ON)}, V_{GS}@-2.5V, I_{DS}@-1.0A=110m\Omega$
- Available in SOT-23S Package

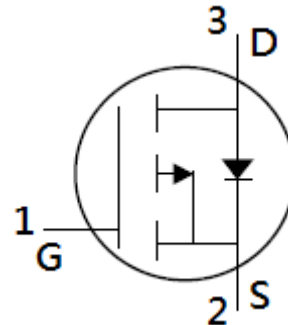
ORDERING INFORMATION

Package Type	Part Number	
SOT-23S	E3S	AM2301AE3SR
		AM2301AE3SVR
Note	V: Halogen free Package R: Tape & Reel	
AiT provides all RoHS products		
Suffix “ V ” means Halogen free Package		

APPLICATION

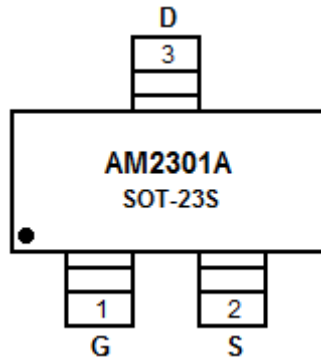
- Advanced trench process technology
- High Density Cell Design For Ultra Low On-Resistance
- ESD Rating of Class 0 (<100V) per Human Body Model

PIN DESCRIPTION





PIN DESCRIPTION



Top View

Pin #	Symbol	Function
1	G	Gate
2	S	Source
3	D	Drain

ABSOLUTE MAXIMUM RATINGS

T_A= 25

V _{DSS} , Drain-to-Source Voltage		-20V
V _{GS} , Gate-to-Source Voltage		±12V
I _D , Continuous Drain Current		-4.7A
I _{DM} , Pulsed Drain Current ^{NOTE1}		-20A
P _D , Maximum Power Dissipation	T _A =25°C	1.1W
	T _A =70°C	0.70W
T _J , T _{STG} , Operation and Storage Temperature Range		-55 ~ +150°C
R _{θJA} , Thermal Resistance-Junction to Ambient ^{NOTE2}		110°C/W

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

NOTE1: Repetitive Rating: Pulse width limited by the Maximum junction temperature

NOTE2: 1-in² 2oz Cu PCB board



ELECTRICAL CHARACTERISTICS

T_A=25°C

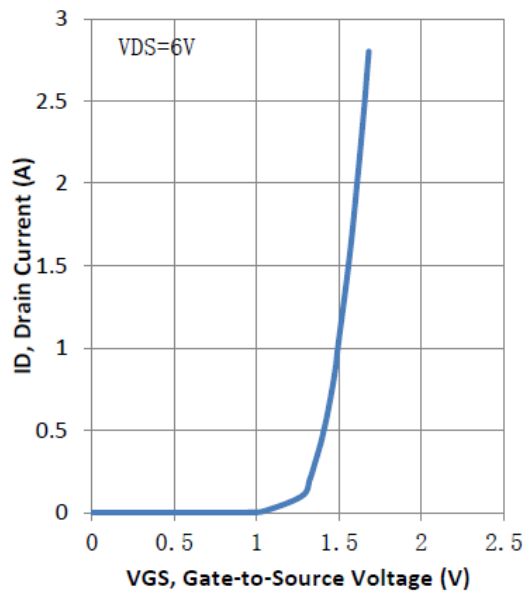
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-20	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =-250uA	-0.6	-0.85	-1.4	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0	-	-	-1	uA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V	-	-	±100	nA
Drain-to-Source On Resistance ^{NOTE3}	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4.7A	-	58	70	mΩ
		V _{GS} =-2.7V, I _D =-3.8A	-	63	90	
		V _{GS} =-2.5V, I _D =-1A	-	75	110	
Forward Diode Voltage	V _{SD}	V _{GS} =0V, I _{SD} =-1.7A	-	-	-1.2	V
DYNAMIC						
Total Gate Charge	Q _g	V _{GS} = -10V, V _{DS} =-4.7V, I _D =-4.5A	-	24	36	nC
Gate-to-Source Gate Charge	Q _{gs}		-	18	-	
Gate-to-Drain Charge	Q _{gd}		-	2.7	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} =-10V, R _L =10Ω, I _D =-1A, V _{GEN} =-4.5V, R _G =6Ω	-	22	35	ns
Rise Time	t _r		-	35	55	
Turn-Off Delay Time	t _{d(off)}		-	45	70	
Fall Time	t _f		-	25	40	
Forward Transconductance	g _{FS}	V _{DS} = -10 V, I _D =-4.7A	-	8	-	S

NOTE3: Pulse Test: Pulse width≤300μs, duty cycle ≤2%.

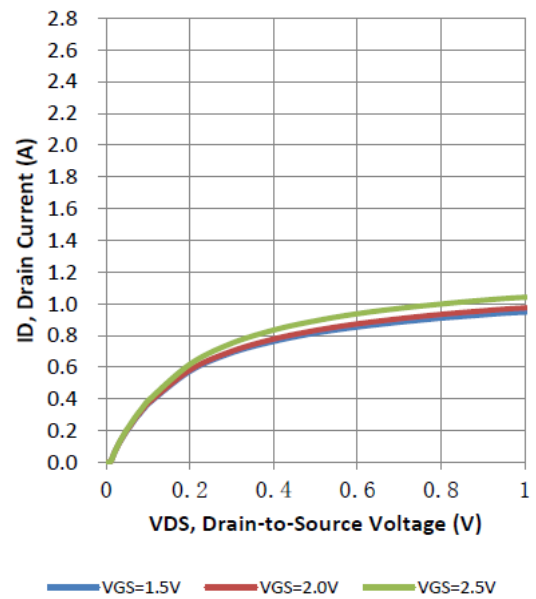


TYPICAL CHARACTERISTICS

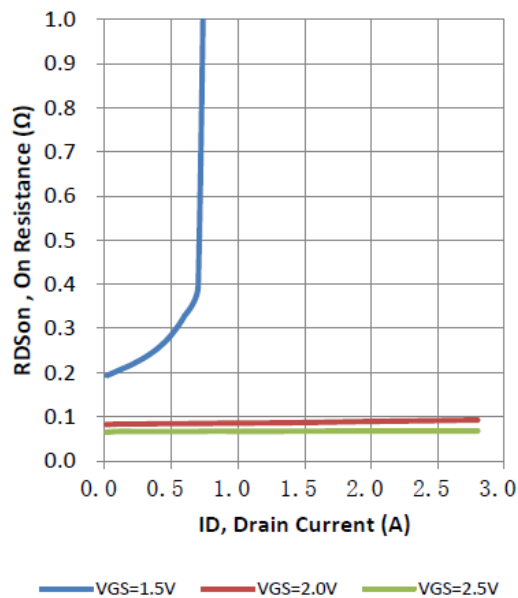
1. Transfer Characteristics



2. On-Region Characteristics



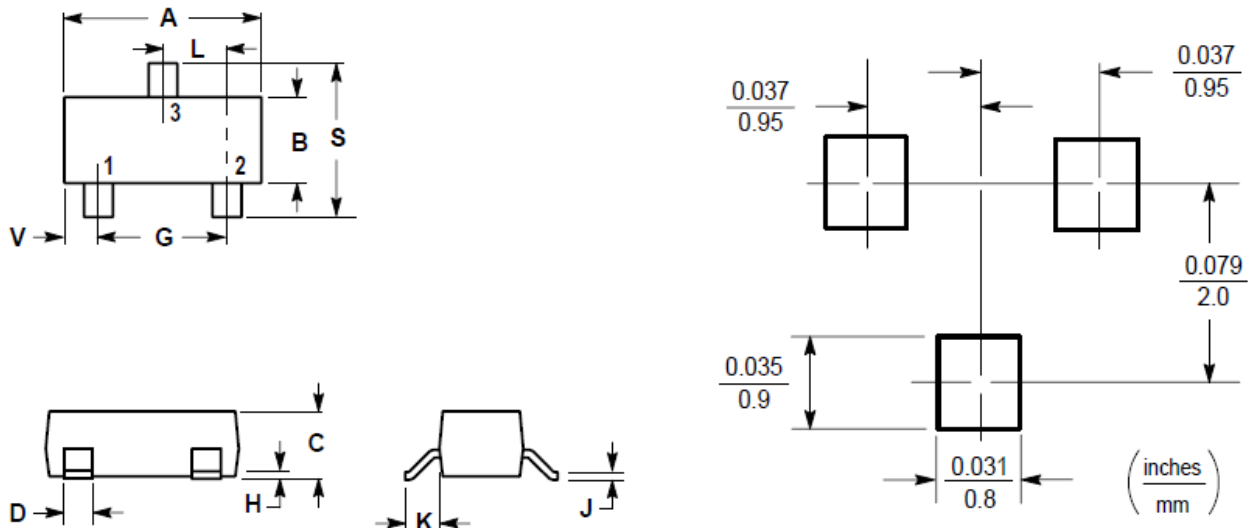
3. On-Resistance Versus Drain Current





PACKAGE INFORMATION

Dimension in SOT-23S Package (Unit: mm)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.800	3.040	0.1102	0.1197
B	1.200	1.400	0.0472	0.0551
C	0.890	1.110	0.0350	0.0440
D	0.370	0.500	0.0150	0.0200
G	1.780	2.040	0.0701	0.0807
H	0.013	0.100	0.0005	0.0040
J	0.085	0.177	0.0034	0.0070
K	0.350	0.690	0.0140	0.0285
L	0.890	1.020	0.0350	0.0401
S	2.100	2.640	0.0830	0.1039
V	0.450	0.600	0.0177	0.0236



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